

	Type	L #	Hits	Search Text
1	BRS	L1	706914	capacitor
2	BRS	L2	412662	(silicon adj nitride)or SiN
3	BRS	L3	993369	silicon
4	BRS	L4	143828	2 same 3
5	BRS	L5	28558	1 and 4
6	BRS	L6	3047	(analog and digital) and 5
7	BRS	L7	59139	amorphous adj silicon
8	BRS	L8	1263	6 and 7
9	IS&R	L9	1	("6707115").PN.
10	BRS	L10	175296	nitride same silicon
11	BRS	L11	560583	integrated adj circuit
12	BRS	L12	32408	1 and 10
13	BRS	L13	15768	11 and 12
14	BRS	L14	1702	6 and 13
15	BRS	L15	20783	(analog and digital) same 11
16	BRS	L16	8152	1 and 15
17	BRS	L17	527	10 and 16
18	BRS	L18	4727	(nitride adj layer) same (silicon adj layer)
19	BRS	L19	1393	1 and 18

	DBs	Time Stamp	Comments	Error Definition
1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	2005/10/10 11:40		
2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	2005/10/10 11:41		
3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	2005/10/10 11:41		
4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	2005/10/10 11:41		
5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	2005/10/10 11:42		
6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	2005/10/10 12:05		
7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	2005/10/10 11:43		
8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	2005/10/10 12:00		
9	USPAT	2005/10/10 12:03		
10	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	2005/10/10 12:03		
11	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	2005/10/10 12:05		
12	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	2005/10/10 12:13		
13	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	2005/10/10 12:04		
14	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	2005/10/10 12:04		
15	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	2005/10/10 12:06		
16	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	2005/10/10 12:06		
17	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	2005/10/10 12:06		
18	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	2005/10/10 12:14		
19	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	2005/10/10 12:14		